

P-Channel Enhancement-Mode MOSFET

DESIGNED FOR:

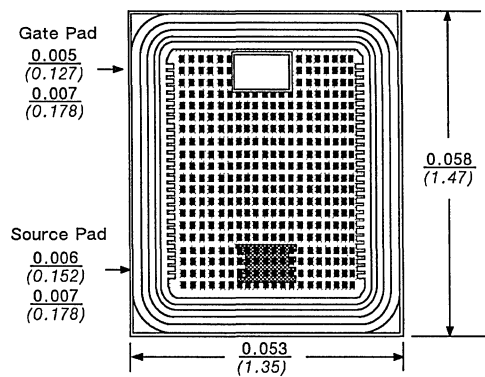
- Switching
- Amplification

FEATURES

- Low $r_{DS(on)} < 5 \Omega$

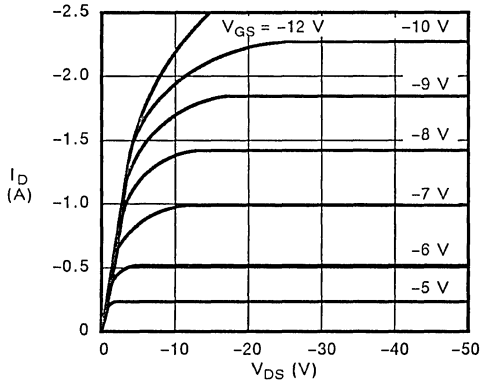
TYPE	PACKAGE	DEVICE
Single	TO-205AD	• VP0808B, VP1008B
	TO-92	• VP0808L, VP1008L
	TO-237	• VP0808M, VP1008M
Quad	14-Pin Plastic	• VQ2004J, VQ2006J
	14-Pin Dual-In-Line	• VQ2004P, VQ2006P
	Chip	• Available as above specifications

GEOMETRY DIAGRAM

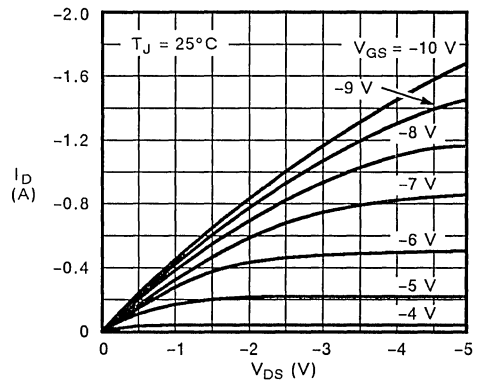


TYPICAL CHARACTERISTICS

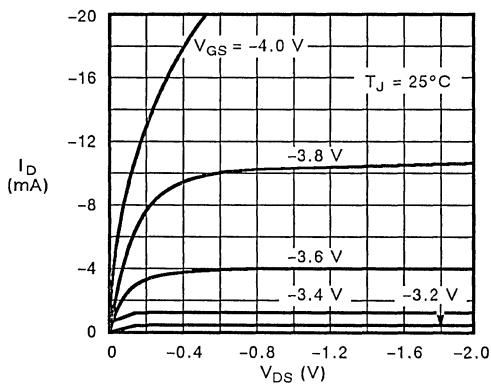
Output Characteristics



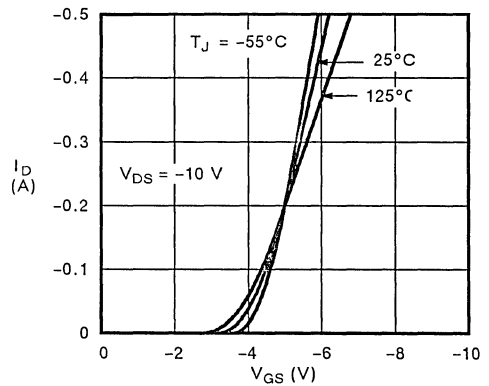
Ohmic Region Characteristics



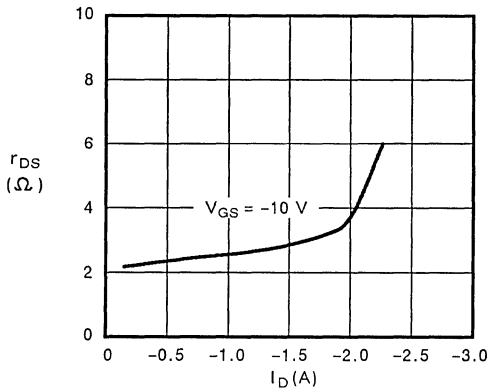
Output Characteristics for Low Gate Drive



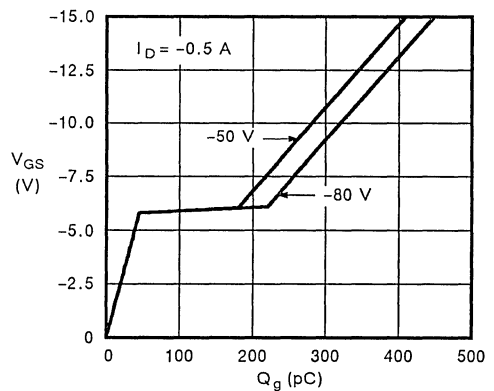
Transfer Characteristics



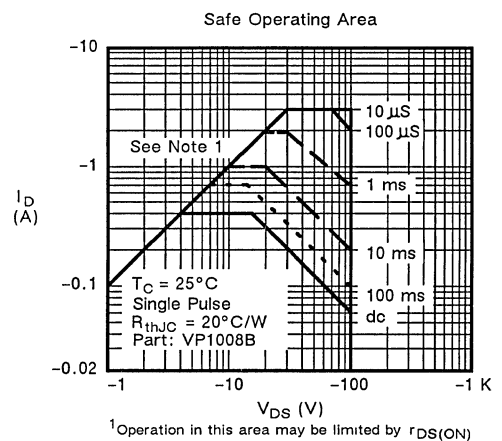
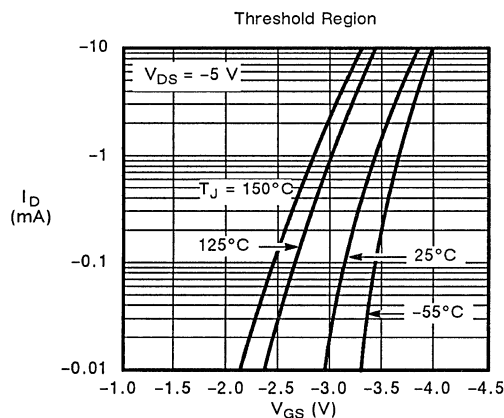
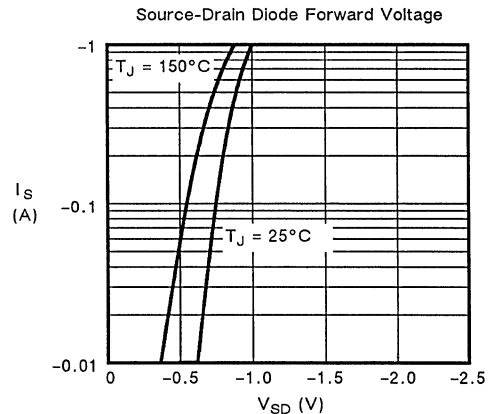
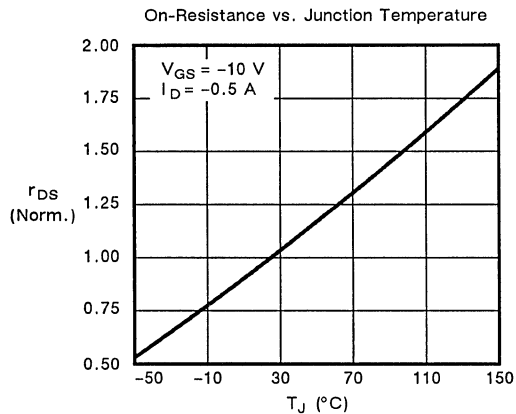
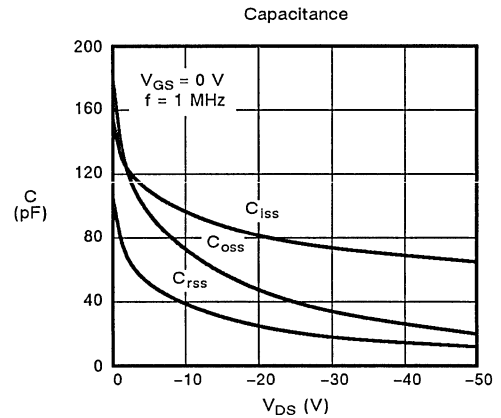
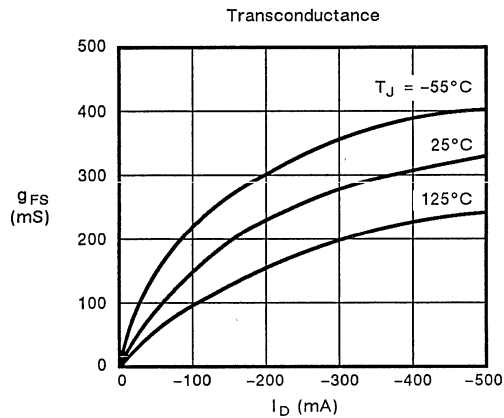
On-Resistance



Gate Charge



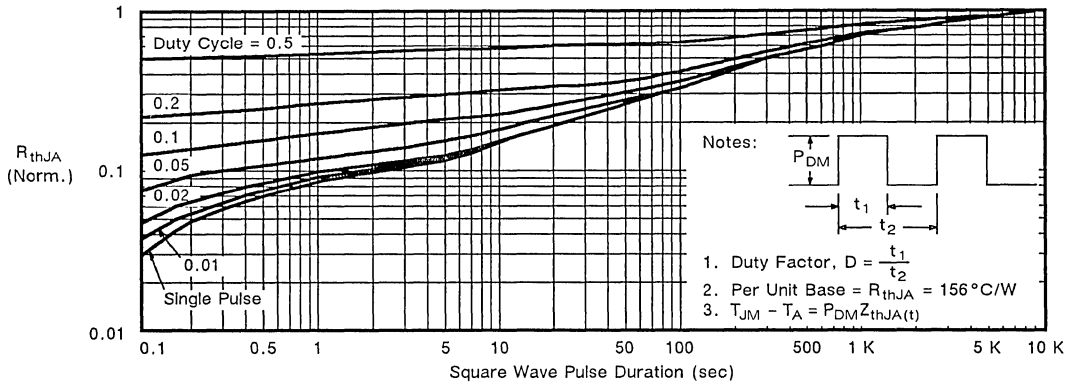
TYPICAL CHARACTERISTICS



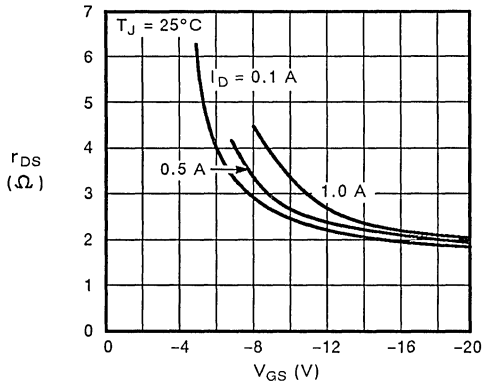
¹Operation in this area may be limited by $r_{DS(ON)}$

TYPICAL CHARACTERISTICS

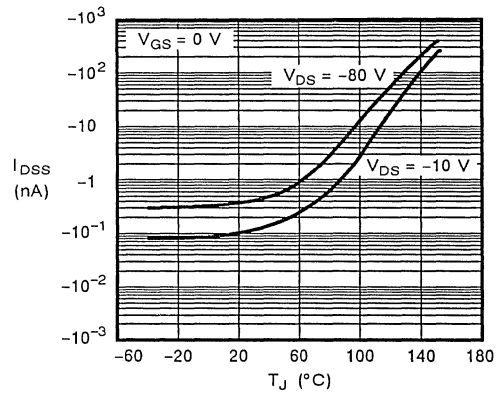
Normalized Effective Transient Thermal Impedance, Junction-to-Ambient (TO-92)



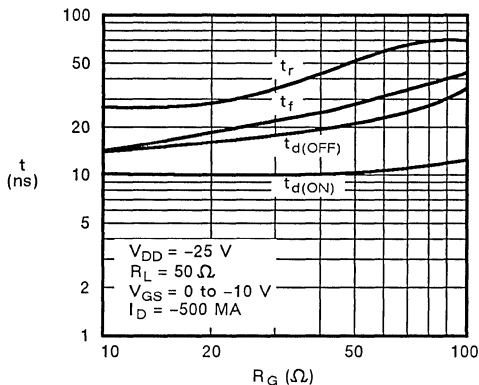
On-Resistance vs. Gate to Source Voltage



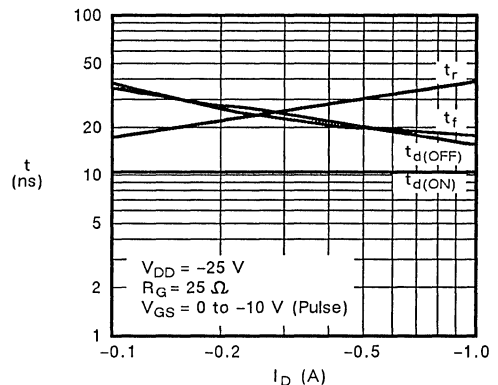
Off State Current



Drive Resistance Effects on Switching



Load Condition Effects on Switching



TYPICAL CHARACTERISTICS

